TENTATIVE

TOSHIBA Photocoupler GaAlAs IRed & Photo-IC

TLP250F

Transistor Inverter
Inverter For Air Conditionor
IGBT Gate Drive
Power MOS FET Gate Drive

The TOSHIBA TLP250F consists of a GaAlAs light emitting diode and a integrated photodetector.

This unit is 8-lead DIP.

TLP250F is suitable for gate driving circuit of IGBT or power MOS FET.

- Input threshold current: IF = 5mA (max.)
- Supply current: 11mA (max.)
- Supply voltage: 10~35V
- Output current: ±1.5A (max.)
- Switching time: tpHL, tpLH = 0.5µs (max.)
- Isolation voltage: 2500 V_{rms} (min.)
- UL recognized: UL1577, file no. E67349
- Option (D4) type

VDE approved: DIN VDE0884 / 06.92、認定 No. 76823 Maximum operating insulation voltage: 1140VPK Highest permissible over voltage: 6000VPK

(Note 1) When a VDE0884 approved type is needed, please designate the "Option (D4)"

• Structural parameter

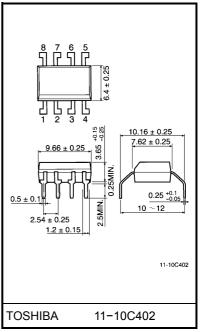
Creepage distance: 8.0mm (min.)

Clearance: 8.0mm (min.)

Truth Table

		Tr1	Tr2
Input LED	On	On	Off
	Off	Off	On

Unit in mm

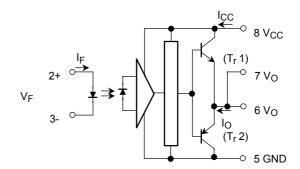


Weight: 0.54 g

Pin Configuration (top view)

8 1: N.C. 2: ANODE 7 3: CATHODE 4: N.C. 5: GND 6 6: V_O (OUTPUT) 7: V_O 8: V_{CC}

Schmatic



(Note 2) A $0.1\mu F$ bypass capcitor must be connected between pin 8 and 5.

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